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INFORMATION DISCLOSURE STATEMENT BY APPLICANT

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Sheet 1 of 1

Complete if Known	
Application Number	10/500,214
Filing Date	June 28, 2004
First Named Inventor	Takuya SUGAWARA
Art Unit	~~2812~~ 2823
Examiner Name	~~Francine Young~~ Michelle Estrada
Attorney Docket Number	010986.55104US

NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No.[1]	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T[2]
	AA	Y. AOKI, ET AL., "In Situ Substrate Surface Cleaning by Low-Energy Ion Bombardment for High Quality Thin Film Formation", J. Vac. Sci. Technol. A, March/April 1993, pp. 307-313, vol. 11 no. 2, American Vacuum Society	
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	AC	KOTARO MIYATANI, ET AL., "A New Plasma Dry Cleaning Method Applied to Contact and Gate Pre Cleaning", Extended Abstracts of the 2002 International Conference on Solid State Devices and Materials, 2002, pp. 196-197, Nagoya	
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	AF	TAKUYA SUGAWARA, ET AL., "Characterization of Ultra Thin Oxynitride Formed by Radical Nitridation with Slot Plane Antenna Plasma", Extended Abstracts of the 2002 International Conference on Solid Devices and Materials, 2002, pp. 714-715, Nagoya	
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	AI	T. NGAL ET AL., "Improving SiO_2/SiGe Intface of SiGe p-metal-oxide-silicon field-effect transistors using water vapor annealing", March 11, 2002, pp. 1773-1775	

Examiner Signature	Michelle Estrada	Date Considered	1/26/06

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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